



POWER SKY (H.K.) LTD.

TO-18 Plastic-Encapsulate Transistors

2SC1162 TRANSISTOR (NPN)

FEATURES

Low frequency power amplifier

MAXIMUM RATINGS ($T_A=25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Value	Units
V_{CBO}	Collector-Emitter Voltage	35	V
V_{CEO}	Collector-Emitter Voltage	35	V
V_{EBO}	Emitter-Base Voltage	5	V
I_C	Collector Current -Continuous	2.5	A
P_C	Collector Power Dissipation	0.75	W
T_J	Junction Temperature	150	$^\circ\text{C}$
T_{stg}	Storage Temperature	-55-150	$^\circ\text{C}$

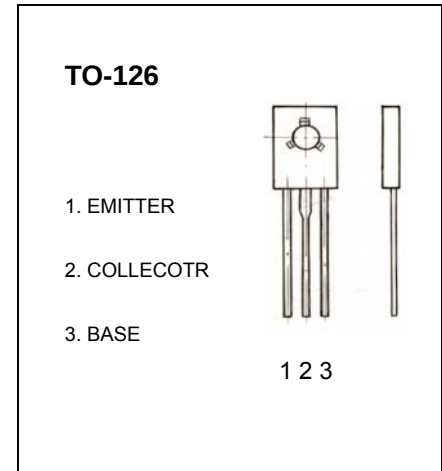
ELECTRICAL CHARACTERISTICS ($T_{amb}=25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=1\text{mA}, I_E=0$	35			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=10\text{mA}, I_B=0$	35			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=1\text{mA}, I_C=0$	5			V
Collector cut-off current	I_{CBO}	$V_{CB}=35\text{V}, I_E=0$			20	μA
Emitter cut-off current	I_{EBO}	$V_{EB}=5\text{V}, I_C=0$			20	μA
DC current gain	h_{FE1}	$V_{CE}=2\text{V}, I_C=0.5\text{A}$	60		320	
	h_{FE2}	$V_{CE}=2\text{V}, I_C=1.5\text{A}^*$	20			
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=2\text{A}, I_B=200\text{mA}$			1	V
Base-collector voltage	V_{BE}	$V_{CE}=2\text{V}, I_C=1.5\text{A}$			1.5	V
Transition frequency	f_T	$V_{CE}=2\text{V}, I_C=200\text{mA}$		180		MHz

* pulse test

CLASSIFICATION OF h_{FE1}

Rank	B	C	D
Range	60-120	100-200	160-320



Typical Characteristics

2SC1162

